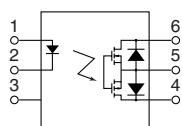
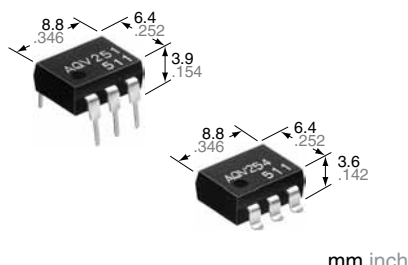


**High sensitivity and low on-resistance.
DIP (1 Form A) 6-pin type.**

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RoHS Directive compatibility information
<http://www.mew.co.jp/ac/e/environment/>

FEATURES

- Highly sensitive and low on-resistance**
- Controls various types of loads such as relays, motors, lamps and solenoids.**
- Optical coupling for extremely high isolation**
5,000 Vrms I/O isolation available.
- Low-level off state leakage current**
- Eliminates the need for a power supply to drive the power MOSFET**
A power supply used to drive the power MOSFET is unnecessary because of the built-in optoelectronic device. This results in easy circuit design and small PC board area.
- Low thermal electromotive force (Approx. 1 μ V)**

TYPICAL APPLICATIONS

- High-speed inspection machines
- Telephone equipment
- Data communication equipment

TYPES

1. I/O isolation voltage: 1,500 V AC

Output rating*		Part No.				Packing quantity	
		Through hole terminal	Surface-mount terminal				
Load voltage	Load current	Tube packing style		Tape and reel packing style		Tube	Tape and reel
				Picked from the 1/2/3-pin side	Picked from the 4/5/6-pin side		
40 V	500 mA	AQV251	AQV251A	AQV251AX	AQV251AZ	1 tube contains 50 pcs. 1 batch contains 500 pcs.	1,000 pcs.
60 V	400 mA	AQV252	AQV252A	AQV252AX	AQV252AZ		
100 V	350 mA	AQV255	AQV255A	AQV255AX	AQV255AZ		
200 V	250 mA	AQV257	AQV257A	AQV257AX	AQV257AZ		
250 V	200 mA	AQV253	AQV253A	AQV253AX	AQV253AZ		
400 V	150 mA	AQV254	AQV254A	AQV254AX	AQV254AZ		
1,000 V	30 mA	AQV259	AQV259A	AQV259AX	AQV259AZ		
1,500 V	20 mA	AQV258	AQV258A	AQV258AX	AQV258AZ		

2. I/O isolation voltage: Reinforced 5,000 V

Output rating*		Part No.				Packing quantity	
		Through hole terminal	Surface-mount terminal				
Load voltage	Load current	Tube packing style		Tape and reel packing style		Tube	Tape and reel
				Picked from the 1/2/3-pin side	Picked from the 4/5/6-pin side		
250 V	200 mA	AQV253H	AQV253HA	AQV253HAX	AQV253HAZ	1 tube contains 50 pcs.	1,000 pcs.
400 V	150 mA	AQV254H	AQV254HA	AQV254HAX	AQV254HAZ	1 batch contains 500 pcs.	

*Indicate the peak AC and DC values.

Note: For space reasons, the SMD terminal shape indicator "A" and the package style indicator "X" or "Z" are not marked on the relay.

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RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

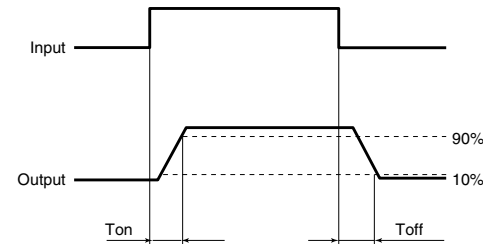
Item		Sym- bol	Type of connection	AQV251(A)	AQV252(A)	AQV255(A)	AQV257(A)	AQV253(A)	AQV254(A)	AQV259(A)	AQV258(A)	AQV253H(A)	AQV254H(A)	Remarks	
Input	LED forward current	I _F		50 mA										f = 100 Hz, Duty factor +0.1%	
	LED reverse voltage	V _R		5 V											
	Peak forward current	I _{FP}		1 A											
	Power dissipation	P _{in}		75 mW											
Output	Load voltage (peak AC)	V _L		40 V	60 V	100 V	200 V	250 V	400 V	1,000 V	1,500 V	250 V	400 V	A connection: Peak AC, DC B, C connection: DC	
	Continuous load current	I _L		A	0.5 A	0.4 A	0.35 A	0.25 A	0.2 A	0.15 A	0.03 A	0.02 A	0.2 A		0.15 A
				B	0.7 A	0.6 A	0.45 A	0.35 A	0.3 A	0.18 A	0.04 A	0.025 A	0.3 A		0.18 A
				C	1.0 A	0.8 A	0.70 A	0.5 A	0.4 A	0.25 A	0.05 A	0.04 A	0.4 A		0.25 A
	Peak load current	I _{peak}			1.8 A	1.5 A	1.0 A	0.75 A	0.6 A	0.5 A	0.09 A	0.06 A	0.6 A		0.5 A
	Power dissipation	P _{out}			360 mW										
Total power dissipation		P _T	410 mW												
I/O isolation voltage		V _{iso}	1,500 V AC										5,000 V AC		
Temperature limits	Operating	T _{opr}	−40°C to +85°C −40°F to +185°F												Non-condensing at low temperatures
	Storage	T _{stg}	−40°C to +100°C −40°F to +212°F												

2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item				Sym- bol	Type of con- nection	AQV251(A)	AQV252(A)	AQV255(A)	AQV257(A)	AQV253(A)	AQV254(A)	AQV259(A)	AQV258(A)	AQV253H(A)	AQV254H(A)	Condition	
Input	LED operate current	Typical	I _{Fon}	—	0.9 mA								1.4 mA		I _L = Max.		
		Maximum			3 mA												
	LED turn off current	Minimum	I _{Foff}	—	0.4 mA											I _L = Max.	
		Typical			0.8 mA								1.3 mA				
LED dropout voltage	Typical	V _F	—	1.25 V (1.14 V at I _F = 5 mA)											I _F = 50 mA		
	Maximum			1.5 V													
Output	On resistance	Typical	R _{On}	A	0.6 Ω	0.74 Ω	1.8 Ω	2.6 Ω	5.5 Ω	12.4 Ω	85 Ω	345 Ω	5.5 Ω	12.4 Ω	I _F = 5 mA I _L = Max. Within 1 s on time		
		Maximum			1 Ω	1.4 Ω	2.5 Ω	4 Ω	8 Ω	16 Ω	200 Ω	500 Ω	8 Ω	16 Ω			
		Typical	R _{On}	B	0.3Ω	0.37 Ω	0.9 Ω	1.4 Ω	2.7 Ω	6.2 Ω	60 Ω	345 Ω	2.7 Ω	6.2 Ω	I _F = 5 mA I _L = Max. Within 1 s on time		
		Maximum			0.5 Ω	0.7 Ω	1.25 Ω	2 Ω	4 Ω	8 Ω	100 Ω	500 Ω	4 Ω	8 Ω			
		Typical	R _{On}	C	0.15 Ω	0.18 Ω	0.45 Ω	0.7 Ω	1.4 Ω	3.1 Ω	30 Ω	160 Ω	1.4 Ω	3.1 Ω	I _F = 5 mA I _L = Max. Within 1 s on time		
		Maximum			0.25 Ω	0.35 Ω	0.63 Ω	1 Ω	2 Ω	4 Ω	50 Ω	250 Ω	2 Ω	4 Ω			
	Off state leak- age current	Maximum	—	—	1 μA						10 μA		1 μA		I _F = 0 mA V _L = Max.		
Transfer characteristics	Switch- ing speed	Turn on time*	T _{On}	—	1.7 ms	1.4 ms	0.9 ms	1.5 ms	0.8ms	0.8ms	0.6ms	0.35 ms	2.4ms	1.8ms	I _F = 5 mA I _L = Max.		
					3 ms		2 ms	3 ms	2 ms		1 ms		4 ms	3 ms			
		Turn off time*	T _{Off}	—	0.07 ms		0.09 ms	0.1 ms	0.06 ms	0.05 ms	0.04 ms		0.06 ms	0.05 ms	I _F = 5 mA I _L = Max.		
					0.2 ms												
	I/O capacitance		Typical	C _{iso}	—	1.3 pF											f = 1 MHz V _B = 0 V
			Maximum			3 pF											
	Initial I/O isola- tion resistance		Minimum	R _{iso}	—	1,000 MΩ											500 V DC

Note: Recommendable LED forward current
Standard type: I_F = 5 mA
Reinforced type: I_F = 5 to 10 mA
*Turn on/Turn off time

For type of connection.



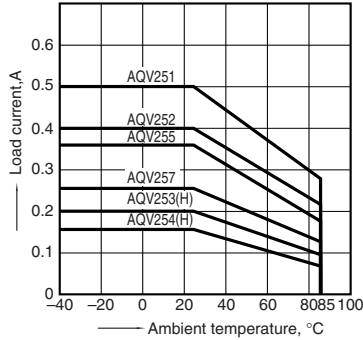
- For Dimensions.
- For Schematic and Wiring Diagrams.
- For Cautions for Use.

REFERENCE DATA

1.-(1) Load current vs. ambient temperature characteristics

Allowable ambient temperature: -40°C to $+85^{\circ}\text{C}$
 -40°F to $+185^{\circ}\text{F}$;

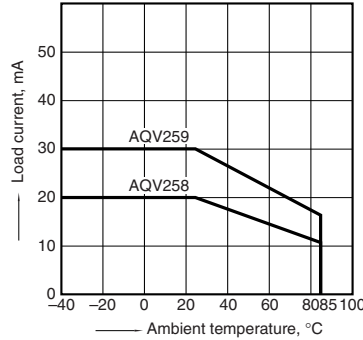
Type of connection: A



1.-(2) Load current vs. ambient temperature characteristics

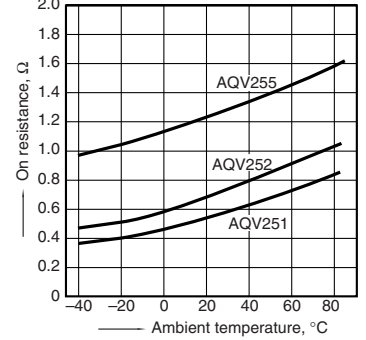
Allowable ambient temperature: -40°C to $+85^{\circ}\text{C}$
 -40°F to $+185^{\circ}\text{F}$;

Type of connection: A



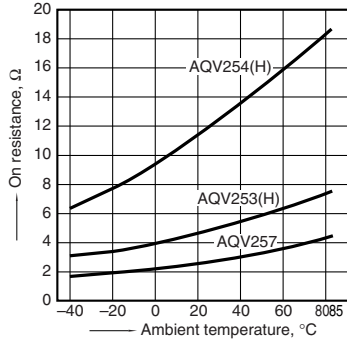
2.-(1) On resistance vs. ambient temperature characteristics

Measured portion: between terminals 4 and 6;
LED current: 5 mA;
Continuous load current: Max. (DC)



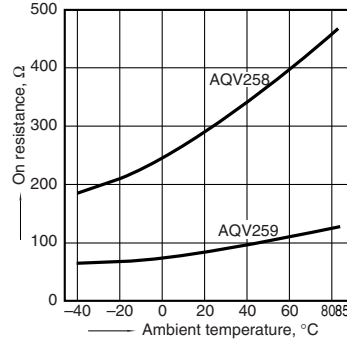
2.-(2) On resistance vs. ambient temperature characteristics

Measured portion: between terminals 4 and 6;
LED current: 5 mA;
Continuous load current: Max. (DC)



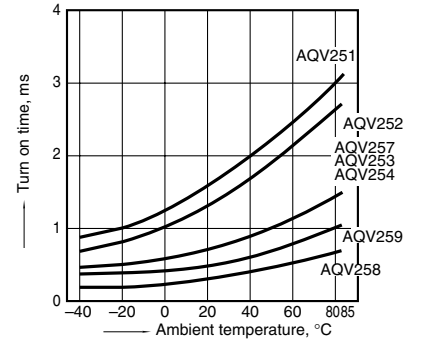
2.-(3) On resistance vs. ambient temperature characteristics

Measured portion: between terminals 4 and 6;
LED current: 5 mA;
Continuous load current: 30 mA (DC)



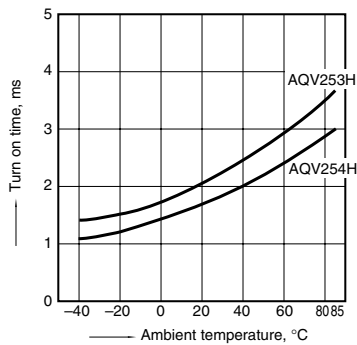
3.-(1) Turn on time vs. ambient temperature characteristics

LED current: 5 mA;
Load voltage: Max. (DC);
Continuous load current: Max. (DC)



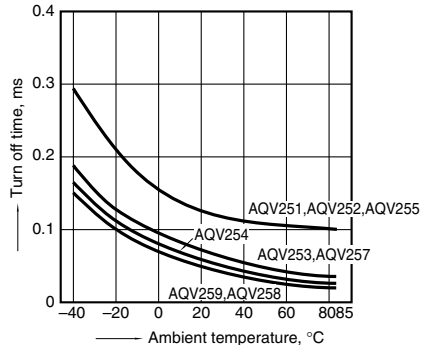
3.-(2) Turn on time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



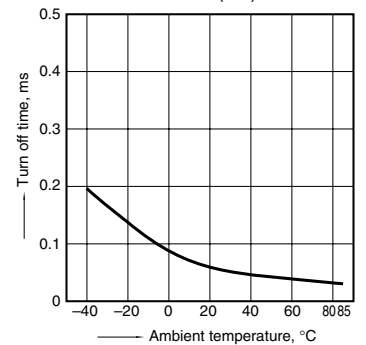
4.-(1) Turn off time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



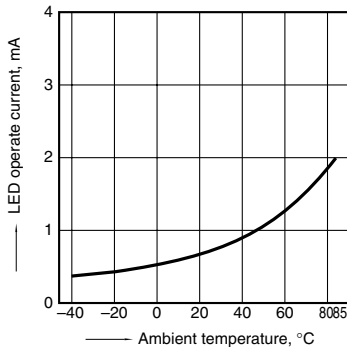
4.-(2) Turn off time vs. ambient temperature characteristics

Sample: AQV253H, AQV254H
LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



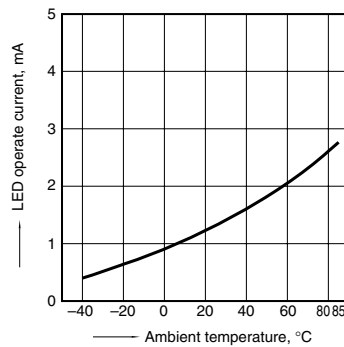
5.-(1) LED operate current vs. ambient temperature characteristics

Sample: AQV251, AQV252, AQV253, AQV254, AQV259; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



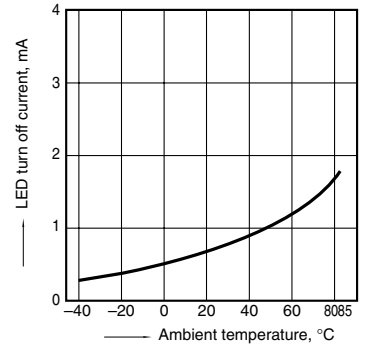
5.-(2) LED operate current vs. ambient temperature characteristics

Sample: AQV253H, AQV254H;
Load voltage: Max. (DC);
Continuous load current: Max. (DC)



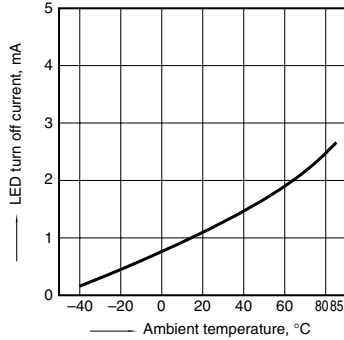
6. -(1) LED turn off current vs. ambient temperature characteristics

Sample: AQV251, AQV252, AQV253, AQV254, AQV259; Load voltage: Max. (DC);
Continuous load current: Max. (DC)

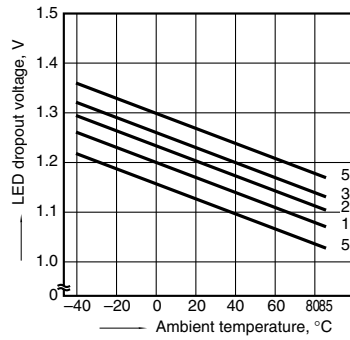


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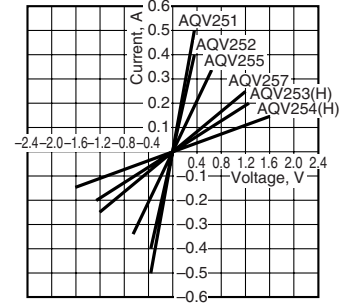
6.-(2) LED turn off current vs. ambient temperature characteristics
Sample: AQV251, AQV252, AQV253, AQV254, AQV259; Load voltage: Max. (DC); Continuous load current: Max. (DC)



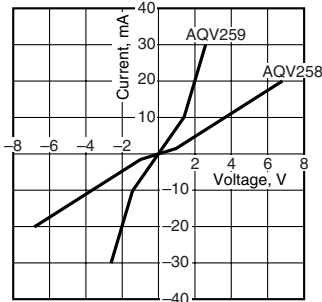
7. LED dropout voltage vs. ambient temperature characteristics
LED current: 5 to 50 mA



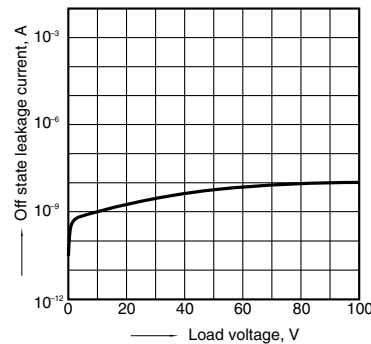
8.-(1) Current vs. voltage characteristics of output at MOS portion
Measured portion: between terminals 4 and 6; Ambient temperature: 25°C 77°F



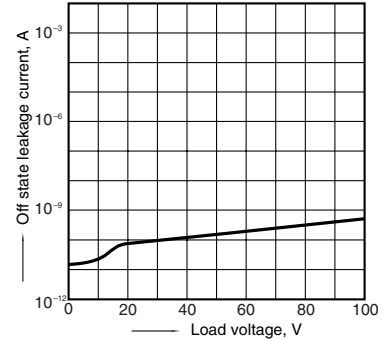
8.-(2) Current vs. voltage characteristics of output at MOS portion
Sample: AQV259
Measured portion: between terminals 4 and 6; Ambient temperature: 25°C 77°F



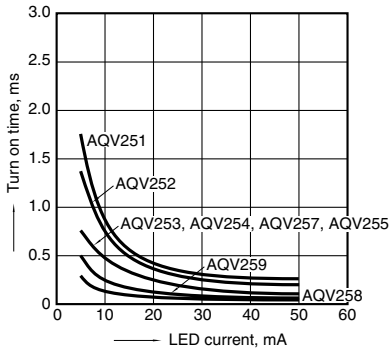
9-(1). Off state leakage current vs. load voltage characteristics
Sample: AQV259;
Measured portion: between terminals 4 and 6; Ambient temperature: 25°C 77°F



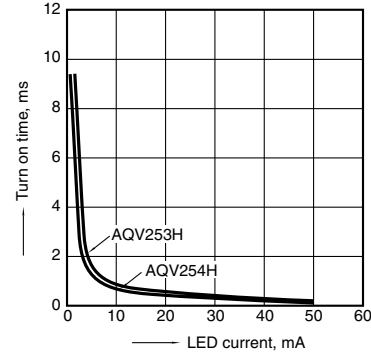
9-(2). Off state leakage current vs. load voltage characteristics
Sample: AQV254H;
Measured portion: between terminals 4 and 6; Ambient temperature: 25°C 77°F



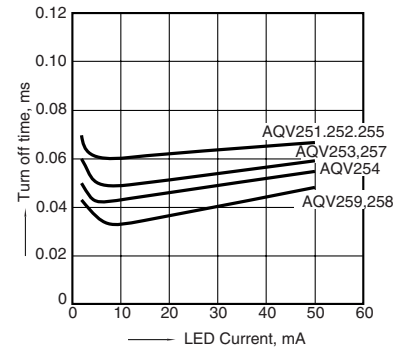
10-(1). Turn on time vs. LED forward current characteristics
Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



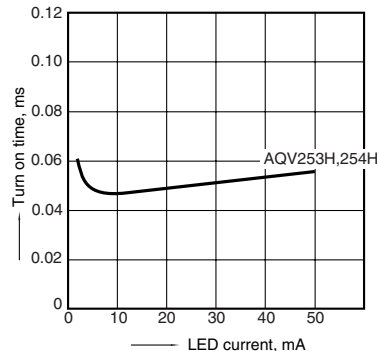
10-(2). Turn on time vs. LED forward current characteristics
Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



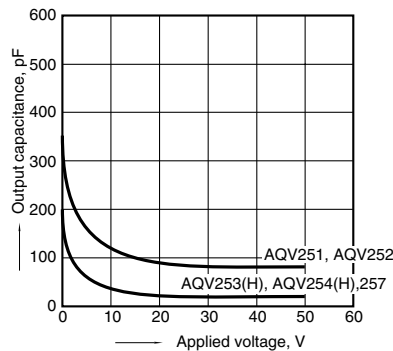
11-(1). Turn off time vs. LED forward current characteristics
Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



11-(2). Turn off time vs. LED forward current characteristics
Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



12.-(1) Output capacitance vs. applied voltage characteristics
Measured portion: between terminals 4 and 6; Frequency: 1 MHz;
Ambient temperature: 25°C 77°F



12.-(2) Output capacitance vs. applied voltage characteristics
Sample: AQV259;
Measured portion: between terminals 4 and 6; Frequency: 1 MHz; Ambient temperature: 25°C 77°F

